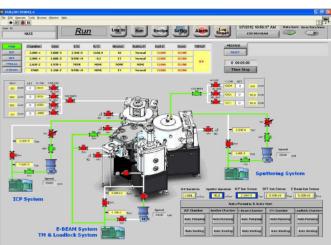
ATS-CVD Series PECVD-PVD Cluster System for Graphene Synthesis





Special Features

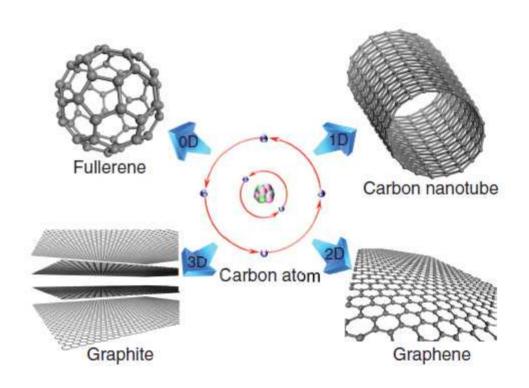
- ◆ Multi-functional cluster system combined with PECVD, sputter and E-beam evaporation for high quality graphene synthesis
- ◆ Maximum substrate heater temperature: 1,000°C for PECVD, 800°C for Sputter and 500°C for e-beam evaporation, respectively
- ◆ Automatic loading transfer chamber around which PECVD, Sputter and E-beam evaporation chambers are attached
- ◆ PC controlled system: recipe save, open function, and fully automation except for e-beam evaporation module
- ◆ Wafer capacity: 8" x1
- ◆ Average throughput: 2,000 wafer/year

Specifications

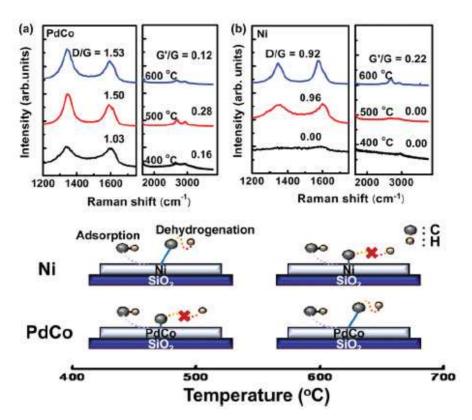
PECVD		
ltem	Specifications	
Source power	2.5kW (13.56MHz)	
Bias power	0.3kW (12.56MHz)	
TMP	1,100ℓ/sec	
Dry pump	9,000ℓ/min	
Substrate heater	SiC coated graphite, Max.1,000℃	
RF ICP coil	2turns	
MFC	CH4(50sccm), H2(200sccm), Ar(200sccm)	
Pressure control	Automatic pressure control system	

Sputter		
ltem	Specifications	
Sputter power	1.5kW (DC)	
Bias power	0.3kW (13.56MHz)	
TMP	1,100ℓ/sec	
Dry pump	9,000ℓ/min	
Substrate heater	SiC coated graphite, Max.800℃	
MFC	Ar(100sccm), O2(50sccm), N2(50sccm)	
Pressure control	Automatic pressure control system	

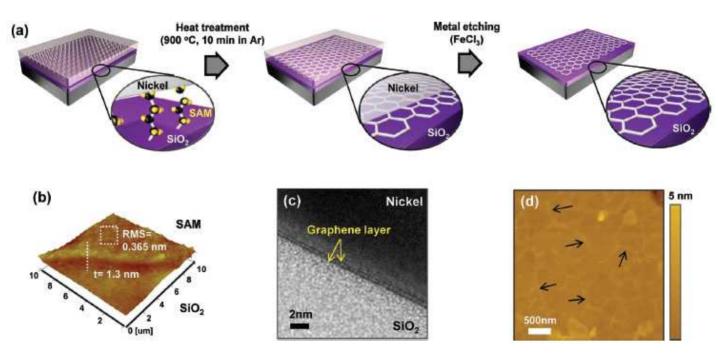
E-beam evaporation		
ltem	Specifications	
E-beam power	10kW(10kV, 1A)	
E-beam gun	4 pocket, 25cc, 180°	
TMP	1,100ℓ/sec	
Dry pump	9,000ℓ/min	
Substrate heater	SiC coated graphite, Max.500℃	
Thickness monitor	SQC310	



Crystal structures of different carbon allotropes

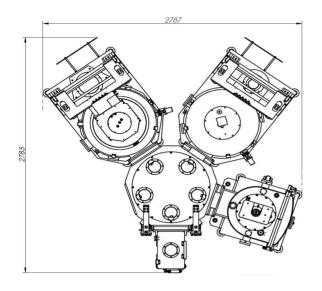


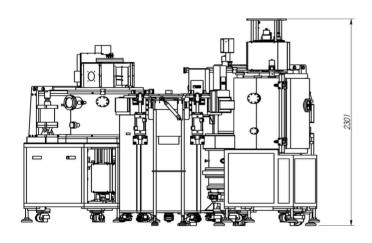
Raman spectra of synthesized graphene film on 100nm PdCo film and 300 nm Ni film on SiO₂ substrate at different temperatures

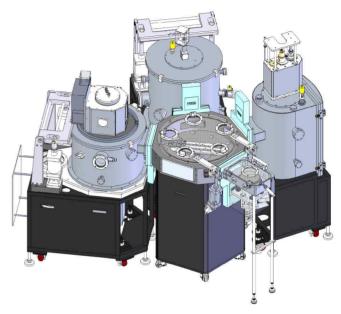


Schematic illustration for transfer-free growth of graphene on a substrate

Layout







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